

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of the Claims**

1. (Currently Amended) A method for forming a contact using a Cu line in semiconductor fabrication, comprising:

forming a dual damascene pattern by etching a pre-metal dielectric (PMD) layer formed on a substrate, wherein the dual damascene pattern includes a contact hole portion located on the substrate and a trench portion located on the contact hole portion, the width of the contact hole portion being narrower than that of the trench portion;

depositing a tungsten diffusion barrier on sidewalls of the dual damascene pattern;

filling the dual damascene pattern with tungsten by depositing tungsten on the tungsten diffusion barrier to form a tungsten layer;

chemical mechanical polishing a portion of the tungsten layer over the trench portion;

etching an upper part of the tungsten layer in the trench portion so as to not expose a void in the contact hole portion, thereby forming a tungsten plug that occupies a lower part of the tungsten layer in the trench portion and the contact hole portion;

depositing a Cu diffusion barrier on the tungsten plug; [[and]]

depositing a Cu on the Cu diffusion barrier[.]; and

removing a portion of the Cu outside of the trench portion by a Cu chemical mechanical polishing process.

2. (Original) A method as defined in claim 1, wherein the tungsten in the trench portion is dry-etched so that the tungsten in the contact hole portion is not exposed.
3. (Original) A method as defined in claim 2, wherein the tungsten diffusion barrier includes a titanium layer and a titanium nitride layer.
4. (Original) A method as defined in claim 3, wherein the Cu diffusion barrier includes a tantalum layer and a tantalum nitride layer.
5. (Cancelled)
6. (Cancelled)
7. (New) A method as defined in claim 4, wherein the tungsten diffusion barrier is a Ti/TiN double layer.
8. (New) A method as defined in claim 7, wherein the thickness of Ti/TiN is 30/5 nm.
9. (New) A method as defined in claim 7, wherein the Cu diffusion barrier is a Ta/TaN double layer.
10. (New) A method as defined in claim 9, wherein the thickness of Ta/TaN is 7.7/7.5 nm.
11. (New) A method as defined in claim 9, wherein the Ti/TiN double layer is thicker than the Ta/TaN double layer.